

RESPONSE TO OFFICE ACTION

Serial No. 10/017,658

Title: HALF DENSITY ROM EMBEDDED DRAM

PAGE 2

Attorney Docket No. 400.105US01

5-7 Cancelled.

8. (Original) The memory device of claim 1 wherein the ROM cell is a capacitor cell hard programmed by physically shorting a storage node of the ROM cell to receive a voltage signal.

9. (Original) A half-density read only memory (ROM) embedded dynamic random access memory (DRAM) device comprising:

a DRAM array comprising first dynamic memory cells;

a ROM array comprising hard programmed non-volatile memory cells and second dynamic memory cells;

sense amplifier circuitry coupled to differential digit lines of the ROM array;

word lines to access rows of the memory ROM array; and

access circuitry to couple one of the non-volatile memory cells and one of the second dynamic memory cells to the differential digit lines in response to a pair of word line signals.

10. (Original) The ROM embedded DRAM device of claim 9 wherein the access circuitry comprises:

a first transistor coupled between the non-volatile memory cells and a first digit line; and

a second transistor coupled between the second dynamic memory cells and a second digit line, wherein gate connections of the first and second transistors are coupled to receive first and second word line signals, respectively.

11. (Original) The ROM embedded DRAM device of claim 9 wherein the non-volatile memory cells are hard programmed to Vcc and the second dynamic memory cells are not programmed.

12. (Original) The ROM embedded DRAM device of claim 9 wherein the non-volatile memory cells are hard programmed to Vss and the second dynamic memory cells are not programmed.

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PAGE 3

Attorney Docket No. 400.105US01

13. (Original) The memory device of claim 9 wherein the ROM cell is a capacitor cell hard programmed,

using an electrical potential to short a dielectric layer of the ROM cell,

using a physical conductor fabricated between capacitor plates of the ROM cell,

using a high leakage path from a storage node of the ROM cell, or

using a physical short between a storage node of the ROM cell to receive a voltage signal.

14. (Previously amended) A half-density read only memory (ROM) comprising:

an array of ROM cells each comprising first and second memory cells, the first memory cell is hard programmed in a non-volatile manner to a first voltage and the second memory cell is a volatile memory cell capacitor; and

access circuitry coupled to read each ROM cell, wherein the access circuitry electrically couples the first and second memory cells to differential sensing circuitry.

15. (Original) The half-density ROM of claim 14 wherein the first voltage has a level of  $V_{cc}$ .

16. (Original) The half-density ROM of claim 14 wherein the first voltage has a level of  $V_{ss}$ .

17. (Previously amended) A method of operating a read-only memory comprising:

programming a first memory cell in a non-volatile manner to a first data state by hard programming the first memory cell to a first voltage level;

providing an un-programmed volatile memory cell; and

accessing both the first and second memory cell capacitors in response to word line signals.

18-20 Cancelled.

21. (Previously amended) The method of claim 17 wherein the first memory cell comprises a plate electrically coupled to the first voltage level.

Cancelled

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PAGE 4

Attorney Docket No. 400.105US01

22. (Previously amended) The method of claim 21 wherein the plate is electrically coupled to the first voltage level that is equal to Vcc or Vss.